



# 安徽富信半导体科技有限公司

ANHUI FOSAN SEMICONDUCTOR TECHNOLOGY CO., LTD.

## US2A THRU US2M

2.0 AMP SURFACE MOUNT HIGH EFFICIENCY RECTIFIERS



### FEATURES

- \* Ideal for surface mount applications
- \* Easy pick and place
- \* Built-in strain relief
- \* Low forward voltage drop

### MECHANICAL DATA

- \* Case: Molded plastic
- \* Epoxy: UL 94V-0 rate flame retardant
- \* Metallurgically bonded construction
- \* Polarity: Color band denotes cathode end
- \* Mounting position: Any
- \* Weight: 0.093 grams

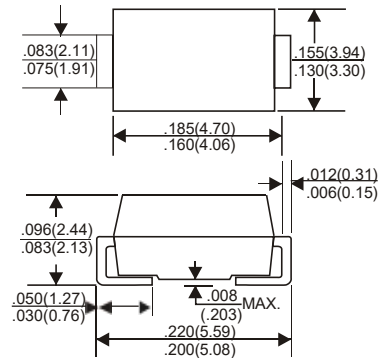
### VOLTAGE RANGE

50 to 1000 Volts

### CURRENT

2.0 Ampere

#### DO-214AA(SMB)



Dimensions in inches and (millimeters)

## MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating 25 °C ambient temperature unless otherwise specified.  
Single phase half wave, 60Hz, resistive or inductive load.  
For capacitive load, derate current by 20%.

TYPE NUMBER	US2A	US2B	US2D	US2E	US2G	US2J	US2K	US2M	UNITS
Maximum Recurrent Peak Reverse Voltage	50	100	200	300	400	600	800	1000	V
Maximum RMS Voltage	35	70	140	210	280	420	560	700	V
Maximum DC Blocking Voltage	50	100	200	300	400	600	800	1000	V
Maximum Average Forward Rectified Current .375"(9.5mm) Lead Length at Ta=50 C	2.0								A
Peak Forward Surge Current, 8.3 ms single half sine-wave superimposed on rated load (JEDEC method)	60								A
Maximum Instantaneous Forward Voltage at 2.0A	1.0		1.3		1.7				V
Maximum DC Reverse Current Ta=25°C	5.0								A
at Rated DC Blocking Voltage Ta=100 C	150								µA
Maximum Reverse Recovery Time (Note 1)	50				70				nS
Typical Junction Capacitance (Note 2)	30								pF
Operating and Storage Temperature Range T <sub>J</sub> , T <sub>STG</sub>	-65—+150								°C

#### NOTES:

1. Reverse Recovery Time test condition: IF=0.5A, IR=1.0A, IRR=0.25A
2. Measured at 1MHz and applied reverse voltage of 4.0V D.C.

## RATING AND CHARACTERISTIC CURVES (US2A THRU US2M)

FIG.1-TYPICAL FORWARD CHARACTERISTICS

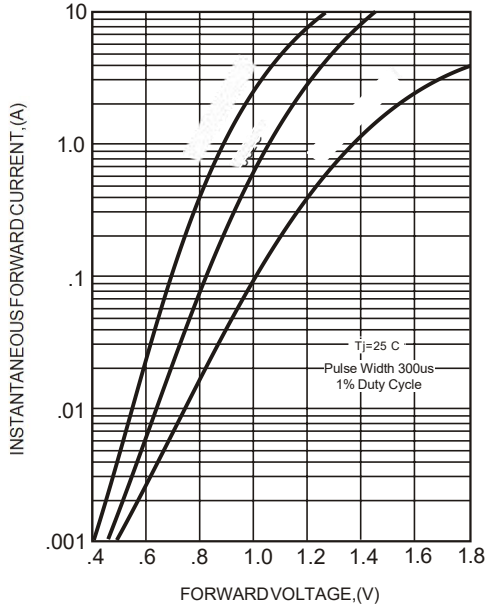


FIG.2-TYPICAL FORWARD CURRENT DERATING CURVE

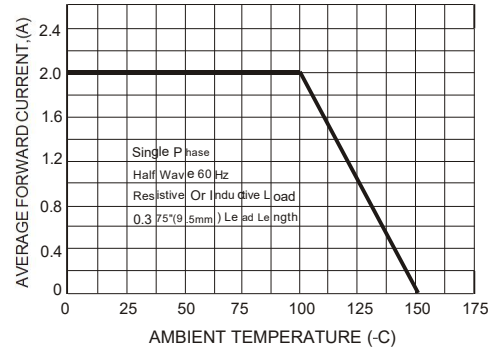
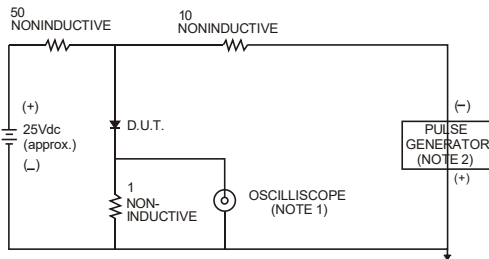


FIG.3- TEST CIRCUIT DIAGRAM AND REVERSE RECOVERY TIME CHARACTERISTICS



NOTES: 1. Rise Time= 7ns max., Input Impedance= 1 megohm.22pF.  
2. Rise Time= 10ns max., Source Impedance= 50 ohms.

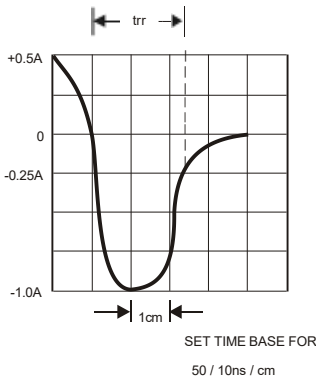


FIG.4-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

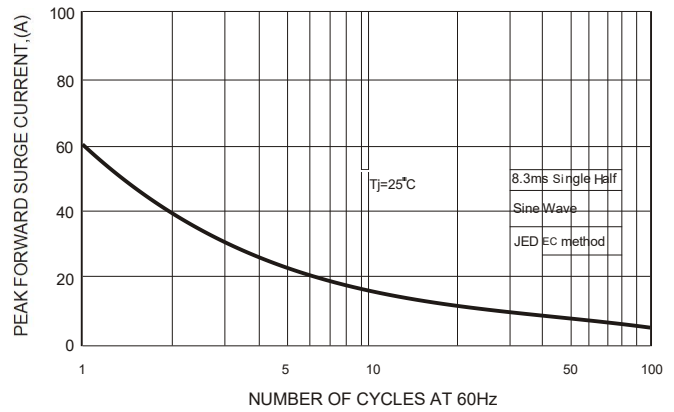


FIG.5-TYPICAL JUNCTION CAPACITANCE

